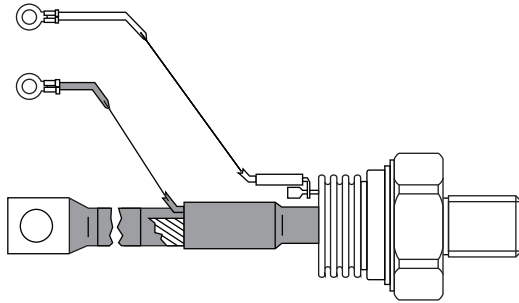


Inverter Grade Thyristors (Stud Version), 330 A



TO-209AE (TO-118)

FEATURES

- Center amplifying gate
- High surge current capability
- Low thermal impedance
- High speed performance
- Compression bonding
- Designed and qualified for industrial level
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912


**RoHS
COMPLIANT**
TYPICAL APPLICATIONS

- Inverters
- Choppers
- Induction heating
- All types of force-commutated converters

PRODUCT SUMMARY

| | |
|--------------------|-------------------|
| $I_{T(AV)}$ | 330 A |
| V_{DRM}/V_{RRM} | 400 V, 2000 V |
| V_{TM} | 1.96 V |
| I_{TSM} at 50 Hz | 11 000 A |
| I_{TSM} at 60 Hz | 11 520 A |
| I_{GT} | 200 mA |
| T_J | -40 °C to 125 °C |
| Package | TO-209AE (TO-118) |
| Diode variation | Single SCR |

MAJOR RATINGS AND CHARACTERISTICS

| PARAMETER | TEST CONDITIONS | VALUES | UNITS |
|-------------------|-----------------|------------|-------------------|
| $I_{T(AV)}$ | | 330 | A |
| | T_C | 75 | °C |
| $I_{T(RMS)}$ | | 518 | A |
| I_{TSM} | 50 Hz | 11 000 | |
| | 60 Hz | 11 520 | |
| I^2t | 50 Hz | 605 | kA ² s |
| | 60 Hz | 550 | |
| V_{DRM}/V_{RRM} | | 400 to 800 | V |
| t_q | | 15 | µs |
| T_J | | -40 to 125 | °C |

ELECTRICAL SPECIFICATIONS
VOLTAGE RATINGS

| TYPE NUMBER | VOLTAGE CODE | V_{DRM}/V_{RRM} , MAXIMUM REPETITIVE PEAK VOLTAGE V | V_{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V | I_{DRM}/I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA |
|-------------|--------------|--|--|--|
| VS-ST333S | 04 | 400 | 500 | 50 |
| | 08 | 800 | 900 | |



| CURRENT CARRYING CAPABILITY | | | | | | | |
|----------------------------------|-----------|-----|-----------|------|-----------|------|----------------|
| FREQUENCY | | | | | | | UNITS |
| 50 Hz | 840 | 600 | 1280 | 1040 | 5430 | 4350 | A |
| 400 Hz | 650 | 450 | 1280 | 910 | 2150 | 1560 | |
| 1000 Hz | 430 | 230 | 1090 | 730 | 1080 | 720 | |
| 2500 Hz | 140 | 60 | 490 | 250 | 400 | 190 | |
| Recovery voltage V_R | 50 | | 50 | | 50 | | V |
| Voltage before turn-on V_D | V_{DRM} | | V_{DRM} | | V_{DRM} | | |
| Rise of on-state current di/dt | 50 | | - | | - | | A/ μ s |
| Case temperature | 50 | 75 | 50 | 75 | 50 | 75 | $^{\circ}$ C |
| Equivalent values for RC circuit | 10/0.47 | | 10/0.47 | | 10/0.47 | | Ω/μ F |

| ON-STATE CONDUCTION | | | | | |
|--|---------------|---|---------------------------|--------|----------------------------|
| PARAMETER | SYMBOL | TEST CONDITIONS | | VALUES | UNITS |
| Maximum average on-state current at case temperature | $I_{T(AV)}$ | 180° conduction, half sine wave | | 330 | A |
| | | | | 75 | $^{\circ}$ C |
| Maximum RMS on-state current | $I_{T(RMS)}$ | DC at 63 $^{\circ}$ C case temperature | | 518 | A |
| Maximum peak, one half cycle, non-repetitive surge current | I_{TSM} | t = 10 ms | No voltage reapplied | 11 000 | |
| | | t = 8.3 ms | No voltage reapplied | 11 520 | |
| | | t = 10 ms | 100 % V_{RRM} reapplied | 9250 | |
| | | t = 8.3 ms | 100 % V_{RRM} reapplied | 9700 | |
| Maximum I^2t for fusing | I^2t | t = 10 ms | No voltage reapplied | 605 | kA ² s |
| | | t = 8.3 ms | No voltage reapplied | 550 | |
| | | t = 10 ms | 100 % V_{RRM} reapplied | 430 | |
| | | t = 8.3 ms | 100 % V_{RRM} reapplied | 390 | |
| Maximum $I^2\sqrt{t}$ for fusing | $I^2\sqrt{t}$ | t = 0.1 ms to 10 ms, no voltage reapplied | | 6050 | kA ² \sqrt{s} |
| Maximum peak on-state voltage | V_{TM} | $I_{TM} = 1810$ A, $T_J = T_J$ maximum, $t_p = 10$ ms sine wave pulse | | 1.96 | V |
| Low level value of threshold voltage | $V_{T(TO)1}$ | $(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$, $T_J = T_J$ maximum | | 0.91 | |
| High level value of threshold voltage | $V_{T(TO)2}$ | $(I > \pi \times I_{T(AV)})$, $T_J = T_J$ maximum | | 0.92 | |
| Low level value of forward slope resistance | r_{t1} | $(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$, $T_J = T_J$ maximum | | 0.58 | m Ω |
| High level value of forward slope resistance | r_{t2} | $(I > \pi \times I_{T(AV)})$, $T_J = T_J$ maximum | | 0.58 | |
| Maximum holding current | I_H | $T_J = 25$ $^{\circ}$ C, $I_T > 30$ A | | 600 | mA |
| Typical latching current | I_L | $T_J = 25$ $^{\circ}$ C, $V_A = 12$ V, $R_a = 6$ Ω , $I_G = 1$ A | | 1000 | |

| SWITCHING | | | | | |
|--|---------|--|--|--------|------------|
| PARAMETER | SYMBOL | TEST CONDITIONS | | VALUES | UNITS |
| Maximum non-repetitive rate of rise of turned-on current | di/dt | $T_J = T_J$ maximum, $V_{DRM} = \text{Rated } V_{DRM}$ $I_{TM} = 2 \times di/dt$ | | 1000 | A/ μ s |
| Typical delay time | t_d | $T_J = 25$ $^{\circ}$ C, $V_{DM} = \text{Rated } V_{DRM}$, $I_{TM} = 50$ A DC, $t_p = 1$ μ s Resistive load, gate pulse: 10 V, 5 Ω source | | 1.0 | μ s |
| Maximum turn-off time | t_q | $T_J = T_J$ maximum, $I_{TM} = 550$ A, commutating $di/dt = 40$ A/ μ s $V_R = 50$ V, $t_p = 500$ μ s, $dV/dt = 200$ V/ μ s | | 15 | |



| BLOCKING | | | | |
|--|--------------------------|---|--------|------------|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS |
| Maximum critical rate of rise of off-state voltage | dV/dt | $T_J = T_J$ maximum, linear to 80 % V_{DRM} , higher value available on request | 500 | V/ μ s |
| Maximum peak reverse and off-state leakage current | I_{RRM} , I_{DRM} | $T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied | 50 | mA |

| TRIGGERING | | | | |
|---|-------------|---|--------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS |
| Maximum peak gate power | P_{GM} | $T_J = T_J$ maximum, $f = 50$ Hz, $d\% = 50$ | 60 | W |
| Maximum average gate power | $P_{G(AV)}$ | | 10 | |
| Maximum peak positive gate current | I_{GM} | $T_J = T_J$ maximum, $t_p \leq 5$ ms | 10 | A |
| Maximum peak positive gate voltage | + V_{GM} | | 20 | V |
| Maximum peak negative gate voltage | - V_{GM} | | 5 | |
| Maximum DC gate current required to trigger | I_{GT} | $T_J = 25$ °C, $V_A = 12$ V, $R_a = 6$ Ω | 200 | mA |
| Maximum DC gate voltage required to trigger | V_{GT} | | 3 | V |
| Maximum DC gate current not to trigger | I_{GD} | $T_J = T_J$ maximum, rated V_{DRM} applied | 20 | mA |
| Maximum DC gate voltage not to trigger | V_{GD} | | 0.25 | V |

| THERMAL AND MECHANICAL SPECIFICATIONS | | | | |
|--|------------|---|-------------------|---------------------|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS |
| Maximum operating junction temperature range | T_J | | -40 to 125 | °C |
| Maximum storage temperature range | T_{Stg} | | -40 to 150 | |
| Maximum thermal resistance, junction to case | R_{thJC} | DC operation | 0.10 | K/W |
| Maximum thermal resistance, case to heatsink | R_{thCS} | Mounting surface, smooth, flat and greased | 0.03 | |
| Mounting torque, ± 10 % | | Non-lubricated threads | 48.5 (425) | N · m (lbf · in) |
| Approximate weight | | | 535 | g |
| Case style | | See dimensions - link at the end of datasheet | TO-209AE (TO-118) | |

| ΔR_{thJ-hs} CONDUCTION | | | | |
|--------------------------------|-----------------------|------------------------|---------------------|-------|
| CONDUCTION ANGLE | SINUSOIDAL CONDUCTION | RECTANGULAR CONDUCTION | TEST CONDITIONS | UNITS |
| 180° | 0.011 | 0.008 | $T_J = T_J$ maximum | K/W |
| 120° | 0.013 | 0.014 | | |
| 90° | 0.017 | 0.018 | | |
| 60° | 0.025 | 0.026 | | |
| 30° | 0.041 | 0.042 | | |

Note

- The table above shows the increment of thermal resistance R_{thJ-hs} when devices operate at different conduction angles than DC

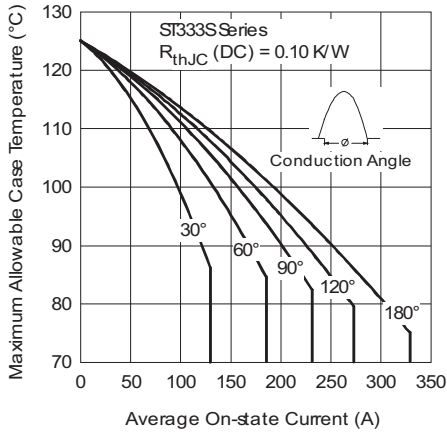


Fig. 1 - Current Ratings Characteristics

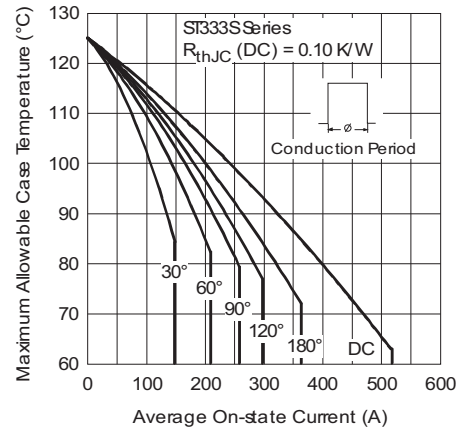


Fig. 2 - Current Ratings Characteristics

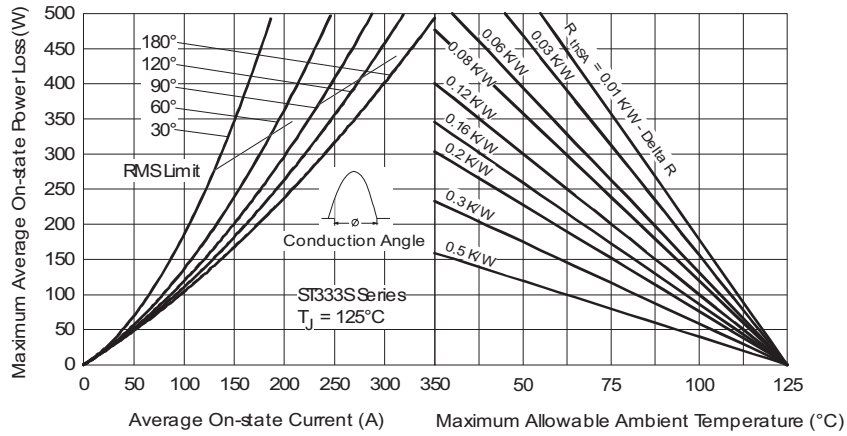


Fig. 3 - On-State Power Loss Characteristics

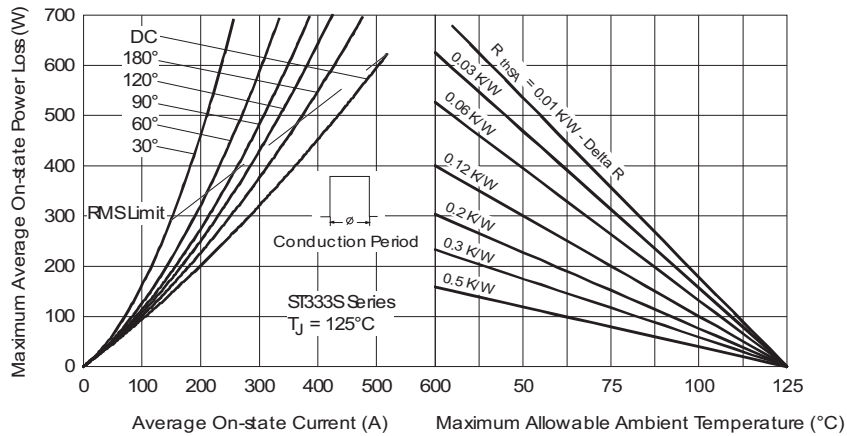


Fig. 4 - On-State Power Loss Characteristics

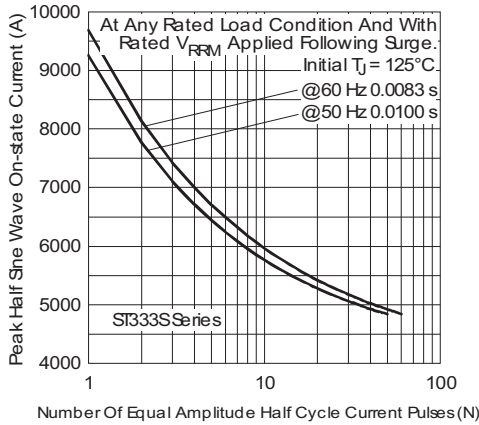


Fig. 5 - Maximum Non-Repetitive Surge Current

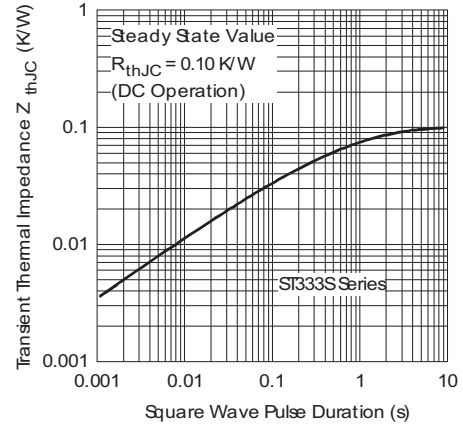


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

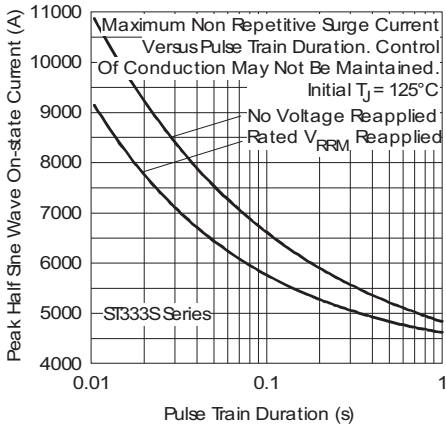


Fig. 6 - Maximum Non-Repetitive Surge Current

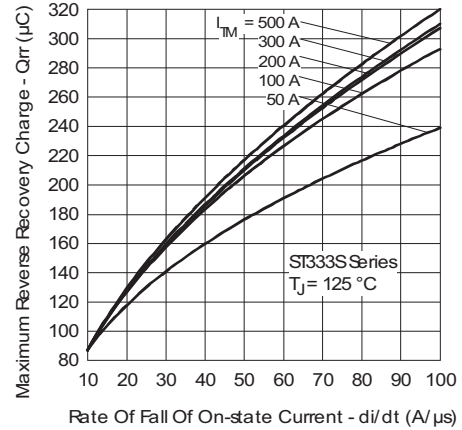


Fig. 9 - Reverse Recovered Charge Characteristics

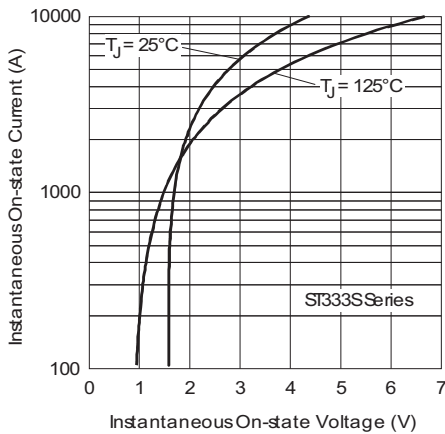


Fig. 7 - On-State Voltage Drop Characteristics

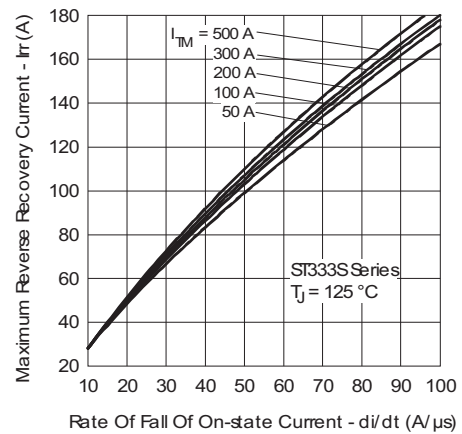


Fig. 10 - Reverse Recovery Current Characteristics

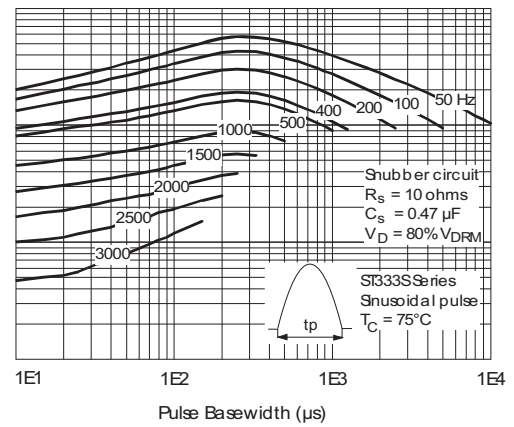
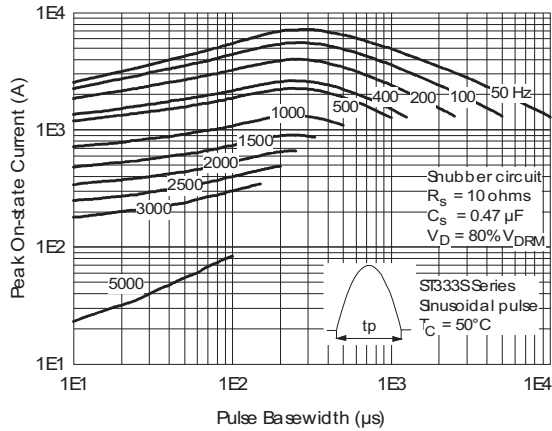


Fig. 11 - Frequency Characteristics

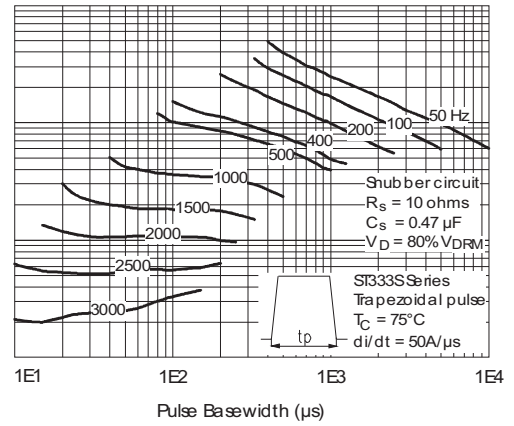
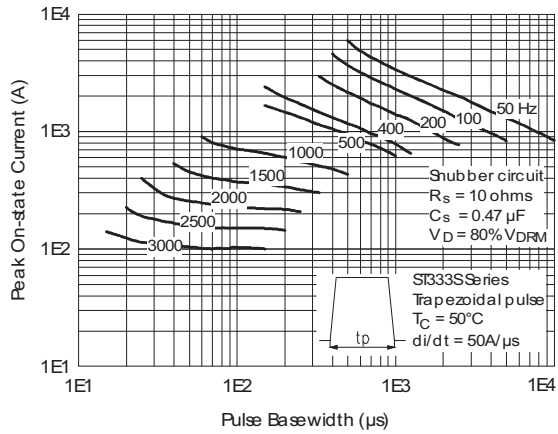


Fig. 12 - Frequency Characteristics

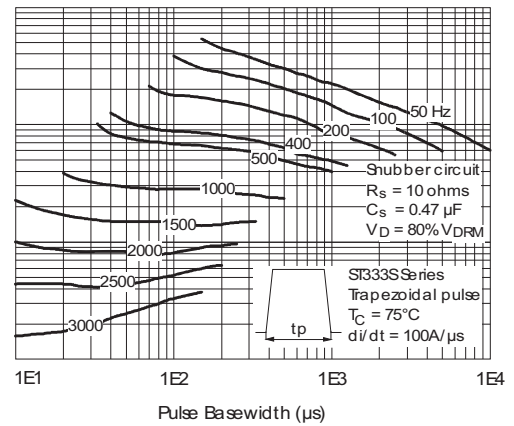
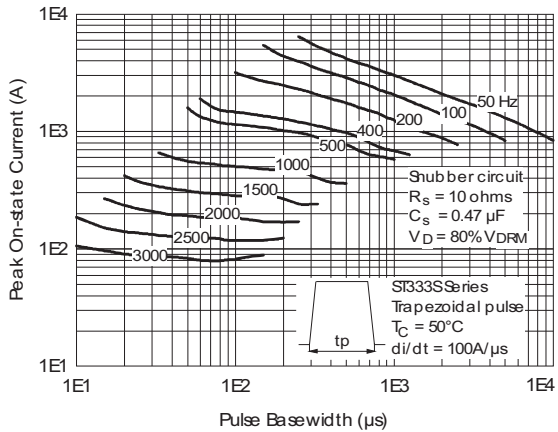


Fig. 13 - Frequency Characteristics

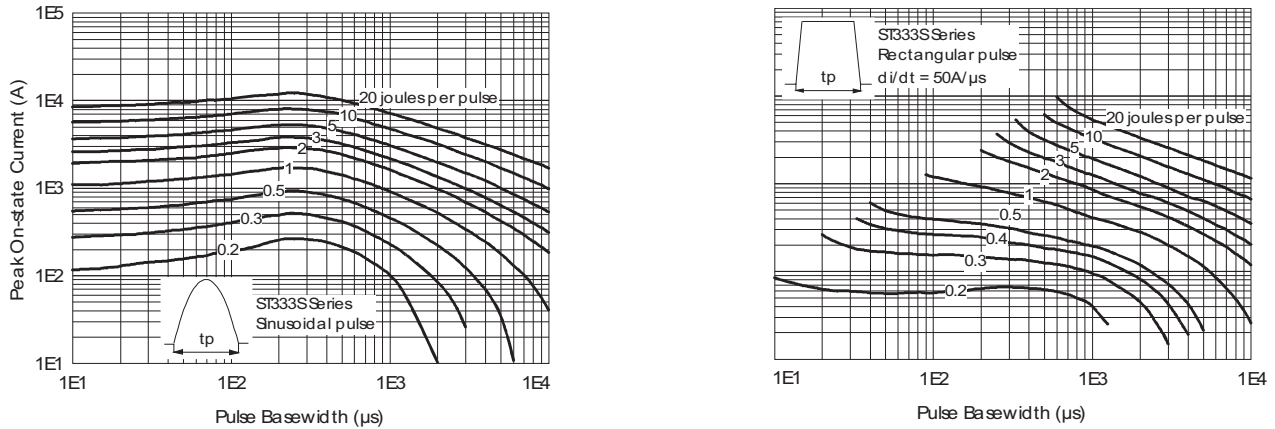


Fig. 14 - Maximum On-State Energy Power Loss Characteristics

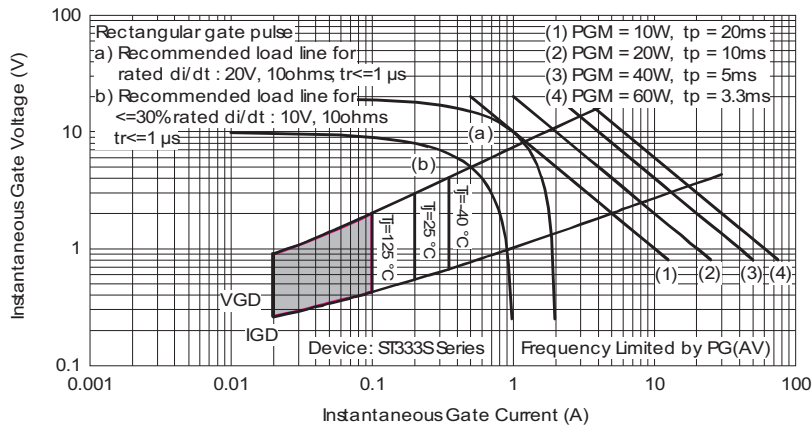
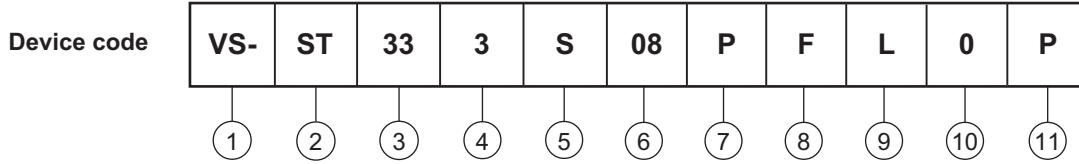


Fig. 15 - Gate Characteristics



ORDERING INFORMATION TABLE



- 1** - Vishay Semiconductors product
- 2** - Thyristor
- 3** - Essential part number
- 4** - 3 = Fast turn-off
- 5** - S = Compression bonding stud
- 6** - Voltage code x 100 = V_{RRM}
(see Voltage Ratings table)
- 7** - P = Stud base 3/4" 16UNF-2A
- 8** - Reapplied dV/dt code (for t_q test condition) $F = 200 \text{ V}/\mu\text{s}$
- 9** - t_q code ($L = 15 \mu\text{s}$)
- 10** - 0 = Eyelet terminals
(gate and auxiliary cathode leads)
1 = Fast-on terminals
(gate and auxiliary cathode leads)
- 11** - None = Standard production
P = Lead (Pb)-free

Note: For metric device M24 x 1.5 contact factory

| LINKS TO RELATED DOCUMENTS | |
|----------------------------|--|
| Dimensions | www.vishay.com/doc?95080 |

TO-209AE (TO-118)

DIMENSIONS in millimeters (inches)



Note

⁽¹⁾ For metric device: M24 x 1.5 - length 21 (0.83) maximum



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- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Помощь Конструкторского Отдела и консультации квалифицированных инженеров;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Поставка электронных компонентов под контролем ВП;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- При необходимости вся продукция военного и аэрокосмического назначения проходит испытания и сертификацию в лаборатории (по согласованию с заказчиком);
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JONHON

«JONHON» (основан в 1970 г.)

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